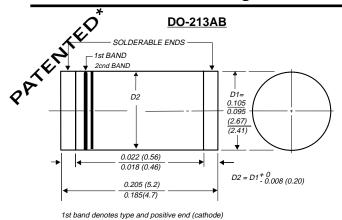
BYM12-50 THRU BYM12-400 EGL41A THRU EGL41G

SURFACE MOUNT GLASS PASSIVATED JUNCTION FAST EFFICIENT RECTIFIER Reverse Voltage - 50 to 400 Volts Forward Current - 1.0 Ampere



Dimensions in inches and (millimeters)
Glass-plastic encapsulation is covered by

Patent No. 3,996,602 and brazed-lead assembly to Patent No. 3,930,306

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Capable of meeting environmental standards of MIL-S-19500
- For surface mount applications
- High temperature metallurgically bonded construction
- Glass passivated cavity-free junction
- Fast switching for high efficiency



 High temperature soldering guaranteed: 450°C/5 seconds at terminals. Complete device submersible temperature of 260°C for 10 seconds in solder bath

MECHANICAL DATA

Case: JEDEC DO-213AB molded plastic over glass body **Terminals:** Plated terminals, solderable per MIL-STD-750, Method 2026

Polarity: Two bands indicate cathode end -1st band denotes device type and 2nd band denotes repetitive peak reverse voltage rating **Mounting Position:** Any

Weight: 0.116 ounce, 0.0046 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

in alle

		SYMBOLS	BYM12 -50	BYM12 -100	BYM12 -150	BYM12 -200	BYM12 -300	BYM12 -400	UNITS
Fast efficient device: 1st band is green			EGL41A	EGL41B	EGL41C	EGL41D	EGL41F	EGL41G	
Polarity color bands (2cnd band)			GRAY	RED	PINK	ORANGE	BROWN	YELLOW	
Maximum repetitive peak reverse voltage		Vrrm	50	100	150	200	300	400	Volts
Maximum RMS voltage		Vrms	35	70	105	140	210	280	Volts
Maximum DC blocking voltage		VDC	50	100	150	200	300	400	Volts
Maximum average forward rectified current at TT=75°C		l(AV)	1.0						Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)		IFSM	30.0						Amps
Maximum instantaneous forward voltage at 1.0A		VF	1.0 1.25				25	Volts	
Maximum DC reverse current at rated DC blocking voltage	T _A =25°C T _A =125°C	I _R			5.0 50.0				μA
Maximum reverse recovery time (NOTE 1)		trr	50.0						ns
Typical junction capacitance (NOTE 2)		CJ	20.0 14.0					pF	
Maximum thermal resistance (NOTE 3) (NOTE 4)		R⊚ja R⊚jt	60.0 30.0						°C/W
Operating junction and storage temperature range		TJ, TSTG	-65 to +175					°C	

NOTES:

(1) Reverse recovery test conditions: IF=0.5A, IR=1.0A, Irr=0.25A

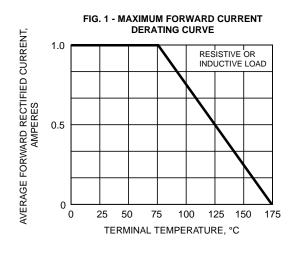
(2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts

(3) Thermal resistance from junction to ambient, 0.24 x 0.24" (6.0 x 6.0mm) copper pads to each terminal

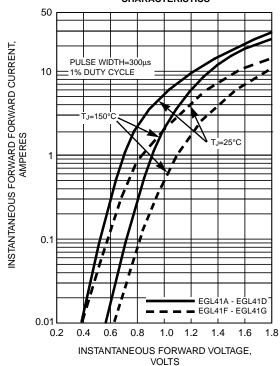
(4) Thermal resistance from junction to terminal, 0.24 x 0.24" (6.0 x 6.0mm) copper pads to each terminal



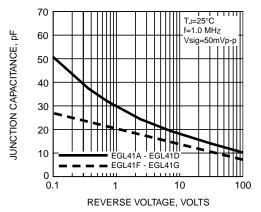
RATINGS AND CHARACTERISTIC CURVES BYM12-50 THRU BYM12-400, EGL41A THRU EGL41G











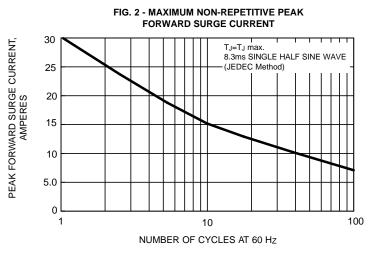
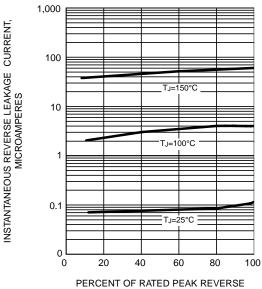
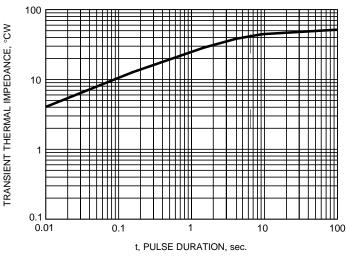


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS



VOLTAGE, %

FIG. 6 - TYPICAL TRANSIENT THERMAL IMPEDANCE



GENERAL SEMICONDUCTOR